Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2549

DC-DC Converter, Relay Drive and Motor Drive **Applications**

• 2.5-V gate drive

: RDS (ON) = 0.29Ω (typ.) Low drain-source ON resistance High forward transfer admittance $|Y_{fs}| = 3.0 \text{ S (typ.)}$ Low leakage current : $I_{DSS} = 100 \,\mu A \,(max) \,(V_{DS} = 16 \,V)$

Enhancement mode : $V_{th} = 0.5 \sim 1.1 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 200 \text{ }\mu\text{A})$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	16	V	
Drain-gate voltage (Ro	_{SS} = 20 kΩ)	V_{DGR}	16	V	
Gate-source voltage		V_{GSS}	±8	٧	
Drain current	DC (Note 1)	I_{D}	2	A	
Diam current	Pulse (Note 1)	I_{DP}	6		
Drain power dissipation	า	P_{D}	0.5	W	
Drain power dissipation (Note 2)		P_{D}	1.5	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Mounted on a ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)

Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

1.6MAX 4.6MAX 0.4 ± 0.05 1.7MAX + 0.08 0.4 - 0.05 1.5 ± 0.1 1.5 ± 0.1

SOURCE **JEDEC**

Weight: 0.05 g (typ.)

DRAIN (HEAT SINK)

1. GATE

JEITA	_
TOSHIBA	2-5K1B

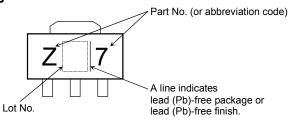
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch-a)}	250	°C/W

This transistor is an electrostatic-sensitive device.

Please handle with caution.

Marking





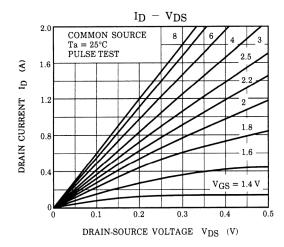
Electrical Characteristics (Ta = 25°C)

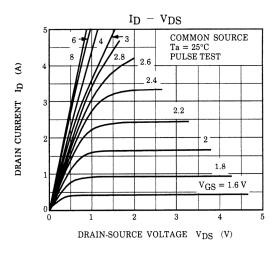
Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±6.5 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	16	_	_	V
Gate threshold v	oltage/	V _{th}	V _{DS} = 10 V, I _D = 200 μA	0.5	_	1.1	V
Drain-source ON resistance	R _{DS (ON)}	V _{GS} = 2.5 V, I _D = 0.5 A		0.29	0.38	Ω	
	INDS (ON)	V _{GS} = 4 V, I _D = 1 A		0.22	0.29		
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1 A	1.5	3.0	_	S
Input capacitano	e	C _{iss}		_	260	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	34	_	pF
Output capacita	nce	C _{oss}		_	103	_	
	Rise time	t _r	$V_{GS} \stackrel{5}{_{0}} V \prod I_{D} = 1 A$ $V_{GS} \stackrel{1}{_{0}} V \prod I_{D} = 1 A$	_	200	_	
Switching time	Turn-on time	t _{on}	$\begin{array}{c c} & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & &$	ı	250	_	ns
Switching time	Fall time	t _f	$\stackrel{\square}{\sim}$ $\stackrel{\square}$	l	300	_	115
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \mu s$	_	800	_	
Total gate charg plus gate-drain)		Qg		_	5.0	_	
Gate-source charge		Q_{gs}	V _{DD} ≈ 16 V, V _{GS} = 5 V, I _D = 2 A		3.2	_	nC
Gate-drain ("mil	ler") charge	Q _{gd}			1.8	_	

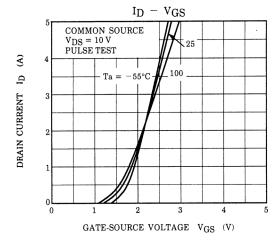
Source-Drain Ratings and Characteristics (Ta = 25°C)

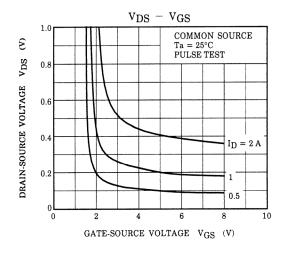
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	-	_	_	2	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	6	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 2 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 2 A, V _{GS} = 0 V	ı	220		ns
Reverse recovered charge	Qrr	dI _{DR} / dt = 50 Å / μs	_	0.32	_	μC

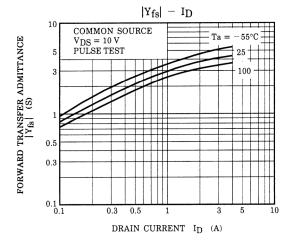
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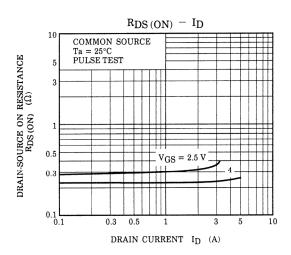


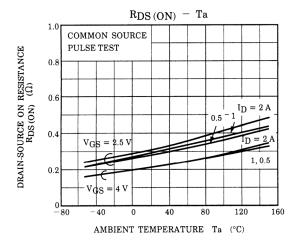


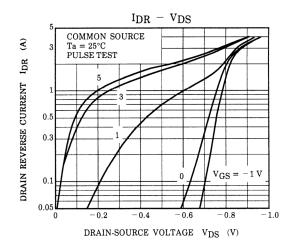


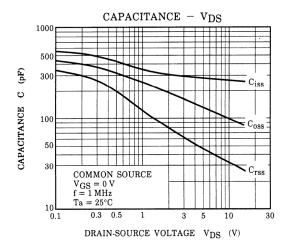


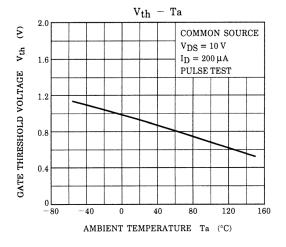


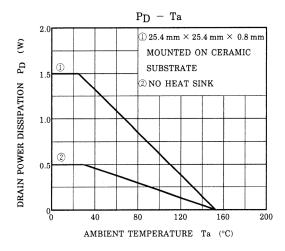




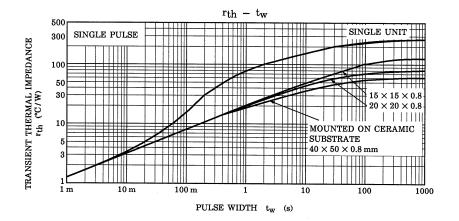


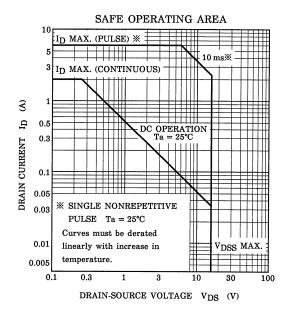






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